



# Micro G Inertial Switch

## Bottom Contact

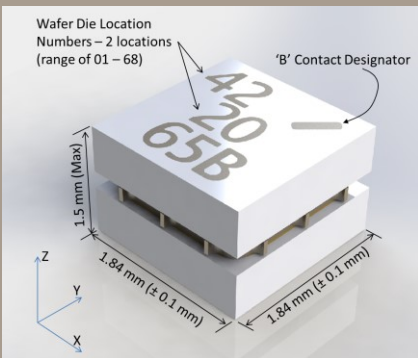
### Model AT-65-B

#### FEATURES:

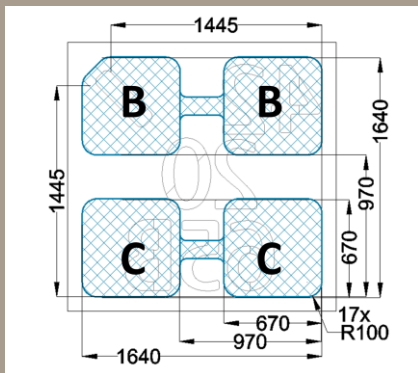
- Small and Lightweight – 3.4 mm<sup>2</sup>
- Extremely Fast Response Times
- High Shock Survivability – 65,000+ g
- Surface Mount – Au over Ni Pads
- Tape and Reel Packaging
- Environmental Seal

#### APPLICATIONS:

- Impact Detection
- Arming / Fuzing
- Artillery, Launch
- More



AT-65-B Device Dimensions



AT-65-B Pad Dimensions (micrometers) as viewed from PAD side of device

## Specifications

#### OPERATING CHARACTERISTICS:

Sensitivity (4) .....	+Z (normal to PCB)	
Contact Acceleration Threshold .....	50 to 80	g
Contact Type (3) .....	Single Pole, Normally Open, Non-Latching	
Response Time (2) .....	< 50	µs
Reset .....	Automatic with g decay	

#### ELECTRICAL CHARACTERISTICS

Contact Resistance (1) .....	< 10	ohms
Insulation Resistance (min.) .....	1000	Mohm
Breakdown Voltage .....	>230	VDC

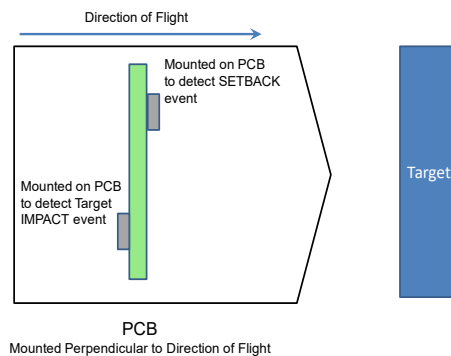
#### ENVIRONMENTAL RATINGS:

Operate Temperature Range .....	-55 to +125	°C
Storage Temperature Range .....	-55 to +125	°C
PCB/Pad Shear Force .....	> 20	N
Shock Survival (5) .....	>65000	g

#### PHYSICAL CHARACTERISTICS:

Dimensions (LxWxH) .....	1.84 x 1.84 x 1.10	mm
Volume .....	3.7	mm <sup>3</sup>
Mass .....	20	milligrams
ROHS Compliant ? .....	Yes	

- (1) Contact resistance is dependent on input pulse acceleration level.
- (2) Response time depends upon input pulse profile
- (3) Electrical connection between pads B (bottom) and C (common) is normally open and is closed while acceleration is greater than the contact acceleration threshold.
- (4) The diagram below provide guidance on how to mount the switch for setback or impact detection
- (5) The Micro G Switch devices are designed to survive the extreme high shock environments associated with artillery launch events.



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